

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Canceled)
2. (Currently Amended) A semiconductor device as set forth in claim ~~[[1]]~~ 4, wherein the lacking portion in the first insulating film is formed near an entire peripheral edge of the semiconductor substrate.
3. (Currently Amended) A semiconductor device as set forth in claim ~~[[1]]~~ 4, wherein the second insulating film covers a side face of the entire layer of the first insulating film in the lacking portion also on a ~~peripheral edge side~~ of the periphery of the semiconductor substrate.
4. (Currently Amended) A semiconductor device ~~as set forth in claim 1,~~
~~further~~ comprising:
a semiconductor substrate having a periphery and a center;
at least one layer of a first insulating film formed above the semiconductor
substrate and having a relative dielectric constant of 3.8 or less, an entire layer of the
first insulating film being separated at least near four corners of the semiconductor
substrate by a lacking portion that extends along the four corners;

a second insulating film covering a side face of the entire layer of the first insulating film in the lacking portion on a side of the center of the semiconductor substrate and having a relative dielectric constant of over 3.8; and

a conductor film layered on the second insulating film in the lacking portion.

5. (Currently Amended) A semiconductor device as set forth in claim 4, further comprising a third insulating film layered on the conductor film and having a relative dielectric constant of over 3.8.

6. (Currently Amended) A semiconductor device ~~as set forth in claim 1,~~
~~wherein the second insulating film also covers~~ comprising:
a semiconductor substrate having a periphery and a center;
at least one layer of a first insulating film formed above the semiconductor substrate and having a relative dielectric constant of 3.8 or less, an entire layer of the first insulating film being separated at least near four corners of the semiconductor substrate by a lacking portion that extends along the four corners;

a second insulating film covering a top face of the first insulating film and a side face of the entire layer of the first insulating film in the lacking portion on a side of the center of the semiconductor substrate and having a relative dielectric constant of over 3.8; and ~~, and the semiconductor device further comprising~~

a conductor pattern passing through the second insulating film on the top face of the first insulating film.

7. (Currently Amended) A semiconductor device as set forth in claim 6, further comprising a second conductor pattern buried in the first insulating film.
8. (Original) A semiconductor device as set forth in claim 6, wherein the conductor pattern contains copper.
9. (Currently Amended) A semiconductor device as set forth in claim ~~[[1]]~~ 4, wherein the first insulating film is constituted of a plurality of layers.
10. (Currently Amended) A semiconductor device as set forth in claim ~~[[1]]~~ 4, wherein the lacking portion in the first insulating film has a width of 0.5 μm or more.
11. (Currently Amended) A semiconductor device as set forth in claim ~~[[1]]~~ 4, wherein the first insulating film ~~on a peripheral edge side~~ between the lacking portion and the periphery of the semiconductor substrate has a width of 0.5 μm or more ~~from the lacking portion~~.
12. (Currently Amended) A semiconductor device as set forth in claim ~~[[1]]~~ 4, wherein a side of the lacking portion in the first insulating film has a length of 1 mm or more.
13. (Canceled)

14. (Currently Amended) A semiconductor device as set forth in claim [[13]] 15, wherein the lacking portion in the first insulating film is formed near an entire peripheral edge of the semiconductor chip.

15. (Currently Amended) A semiconductor device ~~as set forth in claim 13,~~
~~further~~ comprising:

a semiconductor substrate;

at least one layer of a first insulating film formed above the semiconductor
substrate and having a relative dielectric constant of 3.8 or less, an entire layer of the
first insulating film being separated at least near four corners of a semiconductor chip by
a lacking portion that extends along the four corners;

a second insulating film formed in the lacking portion and on the first insulating
film and having a relative dielectric constant of over 3.8; and

a conductor film layered on the second insulating film in the lacking portion.

16. (Original) A semiconductor device as set forth in claim 15, further comprising a third insulating film layered on the conductor film and having a relative dielectric constant of over 3.8.

17. (Currently Amended) A semiconductor device as set forth in claim [[13]] 15, wherein the first insulating film is constituted of a plurality of layers.

18. (Currently Amended) A semiconductor device as set forth in claim [[13]] 15, wherein the lacking portion in the first insulating film has a width of 0.5 μm or more.

19. (Currently Amended) A semiconductor device as set forth in claim [[13]] 15, wherein the first insulating film between the lacking portion and a peripheral edge of the semiconductor chip has a width of 0.5 μm or more from the lacking portion.

20. (Currently Amended) A semiconductor device as set forth in claim [[13]] 15, wherein a side of the lacking portion in the first insulating film has a length of 1 mm or more.

21. (New) A semiconductor device as set forth in claim 6, wherein the lacking portion in the first insulating film is formed near an entire peripheral edge of the semiconductor substrate.

22. (New) A semiconductor device as set forth in claim 6, wherein the second insulating film covers a side face of the entire layer of the first insulating film in the lacking portion on a side of the periphery of the semiconductor substrate.

23. (New) A semiconductor device as set forth in claim 6, further comprising a conductor film layered on the second insulating film in the lacking portion.

24. (New) A semiconductor device as set forth in claim 6, wherein the first insulating film comprises a plurality of layers.

25. (New) A semiconductor device as set forth in claim 6, wherein the lacking portion in the first insulating film has a width of 0.5 μm or more.

26. (New) A semiconductor device as set forth in claim 6, wherein the first insulating film between the lacking portion and the periphery of the semiconductor substrate has a width of 0.5 μm or more.

27. (New) A semiconductor device as set forth in claim 6, wherein a side of the lacking portion in the first insulating film has a length of 1 mm or more.